N-Channel MOSFET

PRODUCT SUMMARY

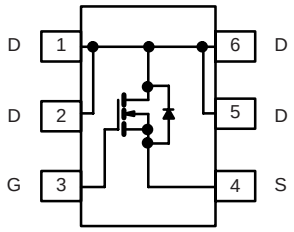
- V_{DS} (V) =30V
- I_D = 6 A
- $R_{DS(ON)}$ < 38mΩ (V_{GS} =10V)
- $R_{DS(ON)}$ < 50mΩ (V_{GS} =4.5V)

FEATURES

- Low On-Resistance

APPLICATIONS

- DC/DC Converters, High Speed Switching



SOT23-6

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	6[e]	A
	T_C = 70 °C		6[e]	
	T_A = 25 °C		5.5[b, c]	
	T_A = 70 °C		4.4[b, c]	
Pulsed Drain Current (t = 300 µs)		I_{DM}	25	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	2.1	
	T_A = 25 °C		1.1[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	2.5	W
	T_C = 70 °C		1.6	
	T_A = 25 °C		1.3[b, c]	
	T_A = 70 °C		0.8[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)			260	

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[b, d]	t ≤ 5 s	R_{thJA}	75	100	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	40	50	

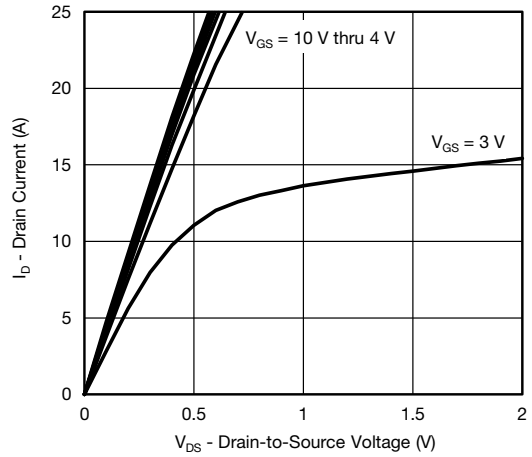
Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 5 s.
d. Maximum under steady state conditions is 166 °C/W.
e. Package limited.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

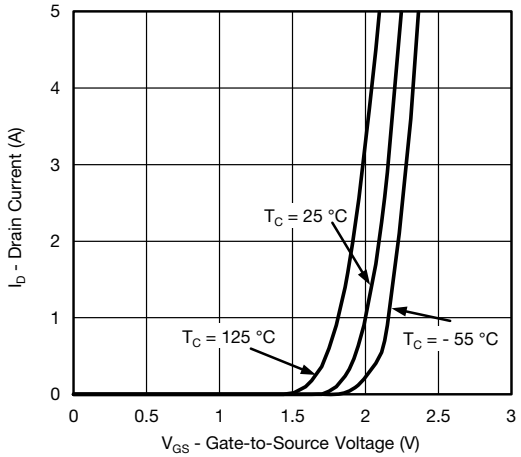
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		30		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 4.8		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D = 250 µA	0.7		1.5	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			1	µA
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 70 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≤ 5 V, V_{GS} = 10 V	20			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 5.5 A		26	30	mΩ
		V_{GS} = 4.5 V, I_D = 5 A		28	40	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 5.5 A		24		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		424		pF
Output Capacitance	C_{oss}			100		
Reverse Transfer Capacitance	C_{rss}			42		
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 5.5 A		8.2	13	nC
		V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 5.5 A		4.2	7	
Gate-Source Charge	Q_{gs}			1.4		
Gate-Drain Charge	Q_{gd}			1.4		
Gate Resistance	R_g	f = 1 MHz	2.5	12.6	25.2	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 3.4 Ω I_D ≅ 4.4 A, V_{GEN} = 4.5 V, R_g = 1 Ω		6	12	ns
Rise Time	t_r			20	30	
Turn-Off Delay Time	$t_{d(off)}$			14	21	
Fall Time	t_f			10	20	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 3.4 Ω I_D ≅ 4.4 A, V_{GEN} = 10 V, R_g = 1 Ω		3	6	
Rise Time	t_r			11	20	
Turn-Off Delay Time	$t_{d(off)}$			20	30	
Fall Time	t_f			7	14	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			2.1	A
Pulse Diode Forward Current	I_{SM}				25	
Body Diode Voltage	V_{SD}	I_S = 4.4 A, V_{GS} = 0 V		0.82	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 4.4 A, dI/dt = 100 A/µs, T_J = 25 °C		13	20	ns
Body Diode Reverse Recovery Charge	Q_{rr}			6	12	nC
Reverse Recovery Fall Time	t_a			8		ns
Reverse Recovery Rise Time	t_b			5		

Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

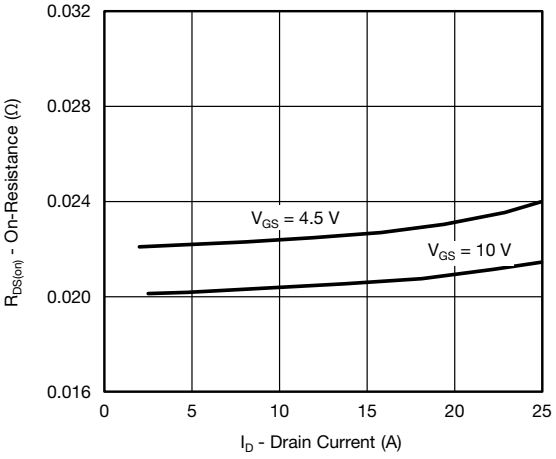
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



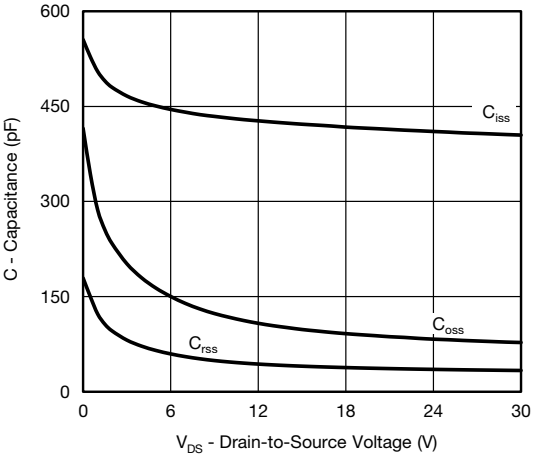
Output Characteristics



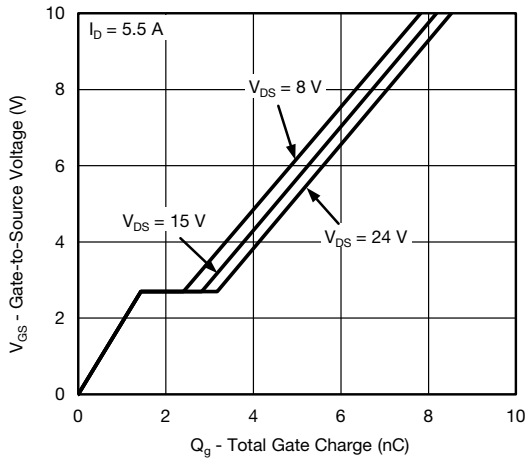
Transfer Characteristics



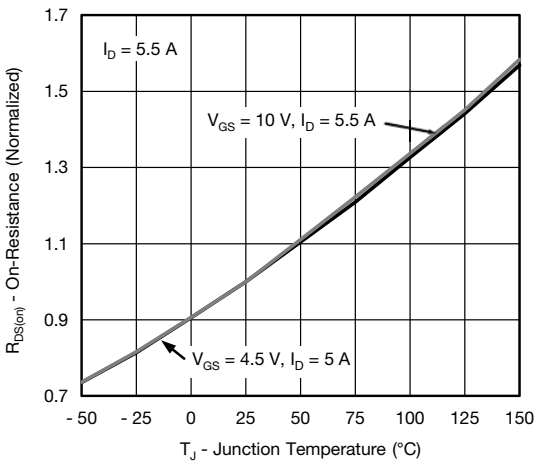
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

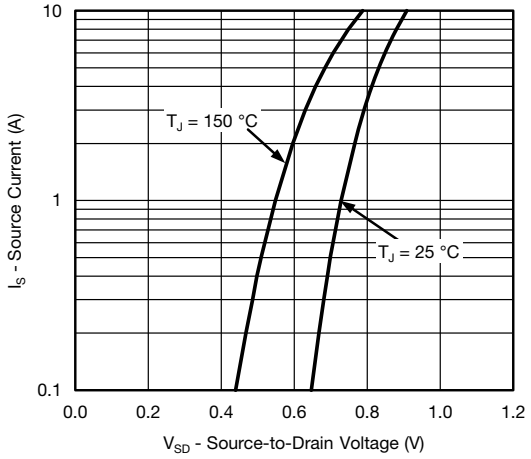


Gate Charge

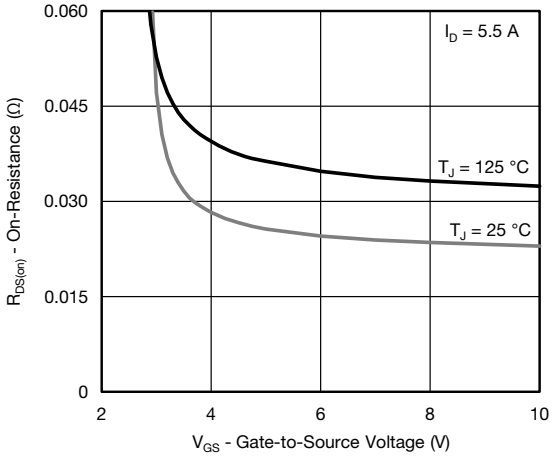


On-Resistance vs. Junction Temperature

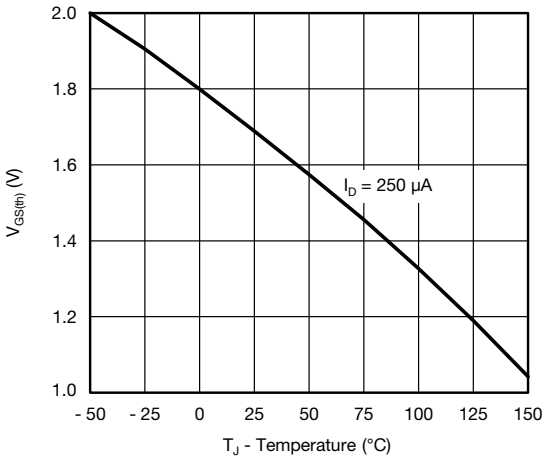
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



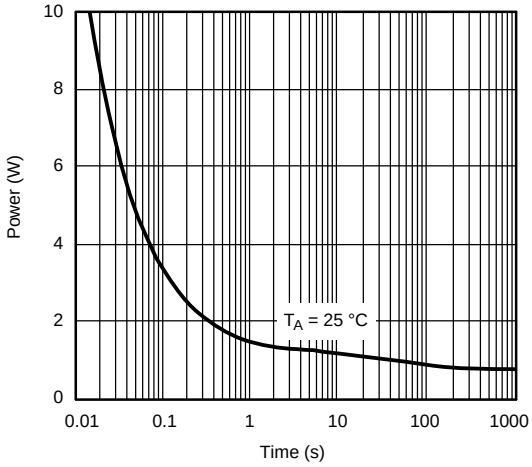
Source-Drain Diode Forward Voltage



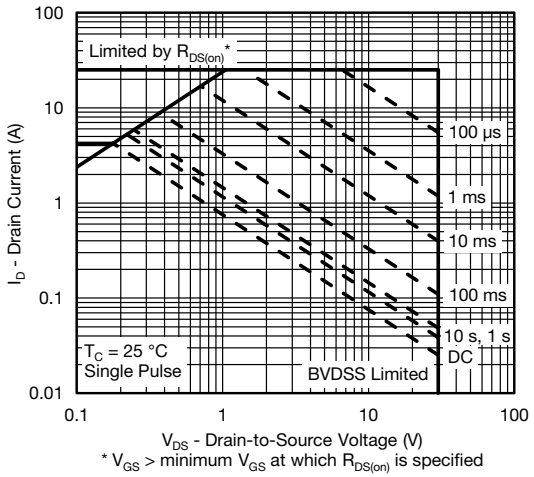
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

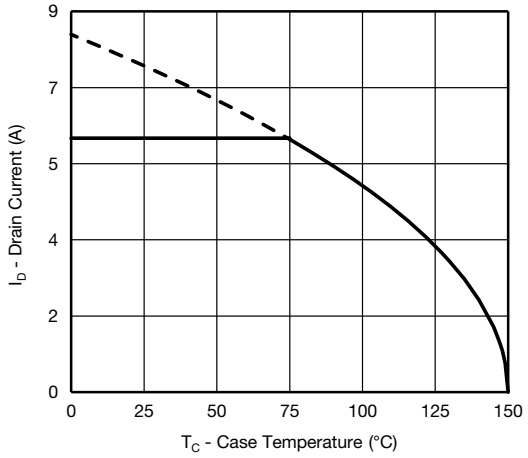


Single Pulse Power (Junction-to-Ambient)

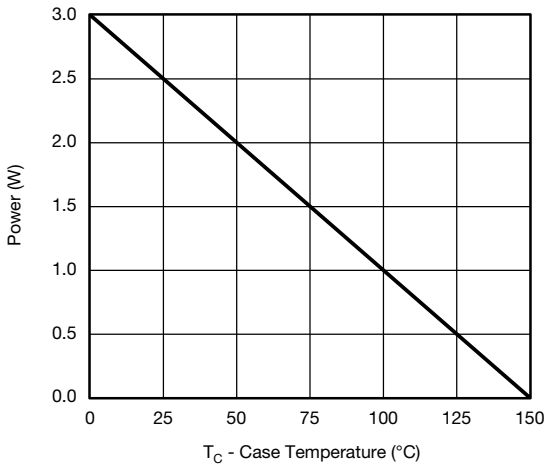


Safe Operating Area, Junction-to-Ambient

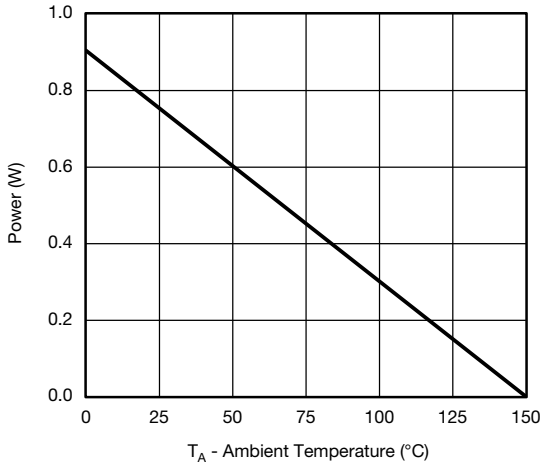
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



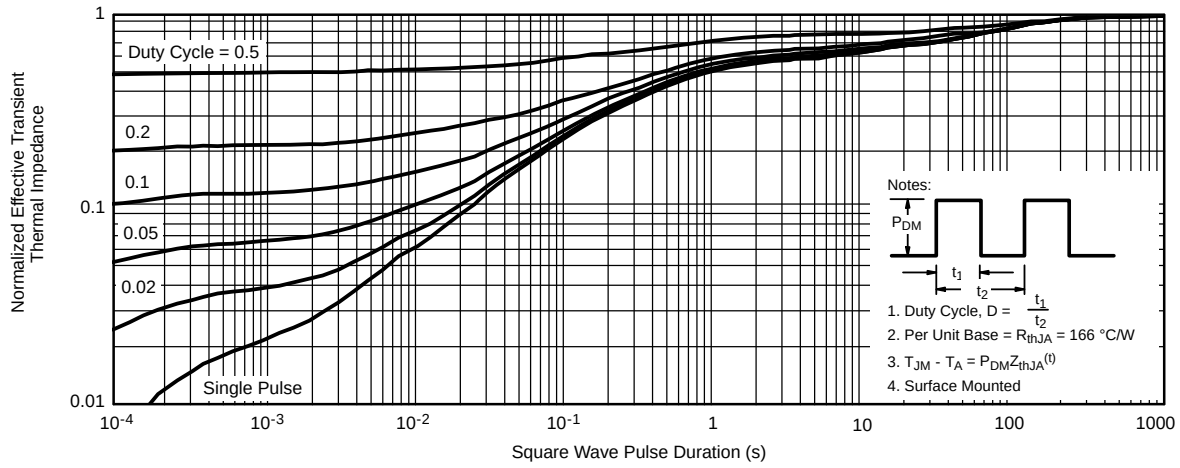
Power Derating, Junction-to-Foot



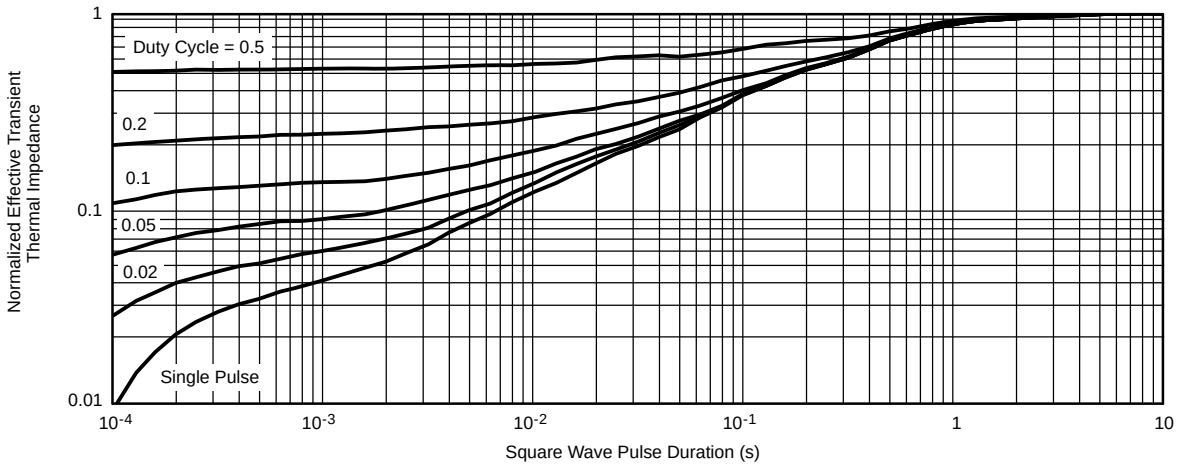
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

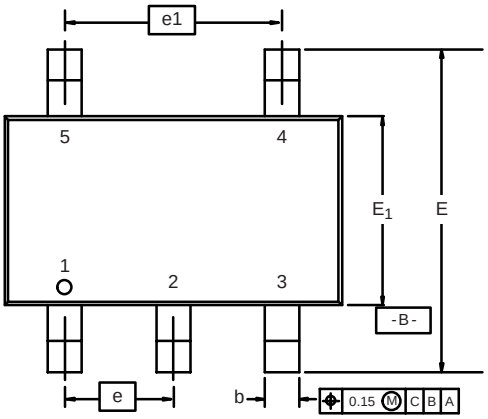


Normalized Thermal Transient Impedance, Junction-to-Ambient

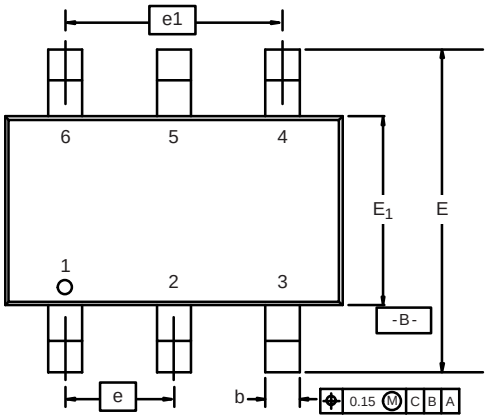


Normalized Thermal Transient Impedance, Junction-to-Foot

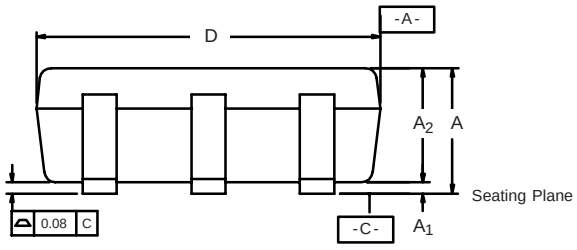
SOT23-5/6 PACKAGE OUTLIE DIMENSIONS

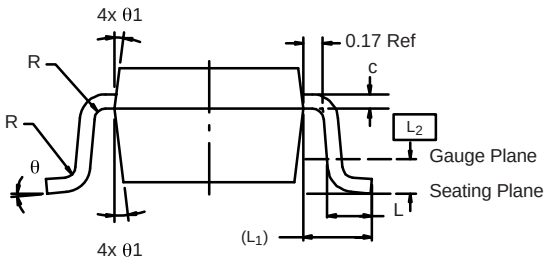


SOT23-5



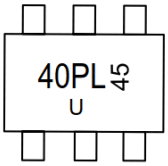
SOT23-6





Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A_1	0.01	-	0.10	0.0004	-	0.004
A_2	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E_1	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e_1	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L_1	0.60 Ref			0.024 Ref		
L_2	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW AO6400	SOT23-6	3000	Tape and reel